PROCESS CPD93V

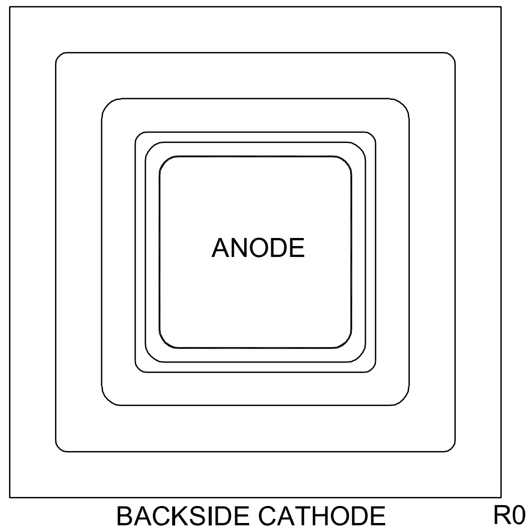
Switching Diode

High Current Switching Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	12.8 x 12.8 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	5.1 x 5.1 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 10,000Å

GEOMETRY



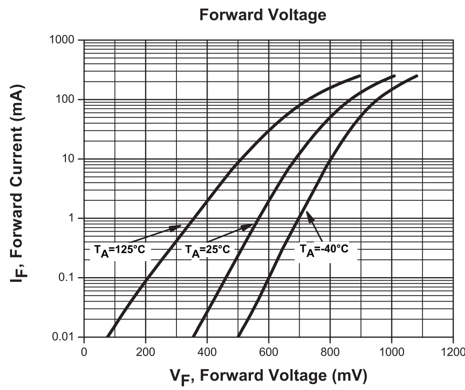
GROSS DIE PER 4 INCH WAFER
63,904

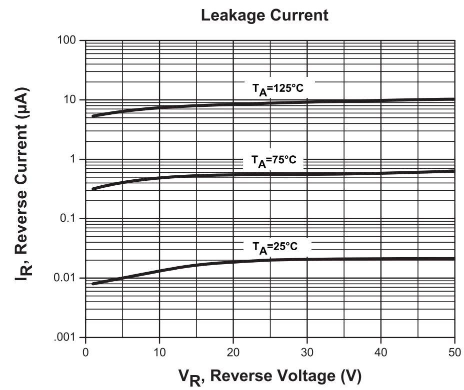
PRINCIPAL DEVICE TYPES
CMPD4150
BAS56

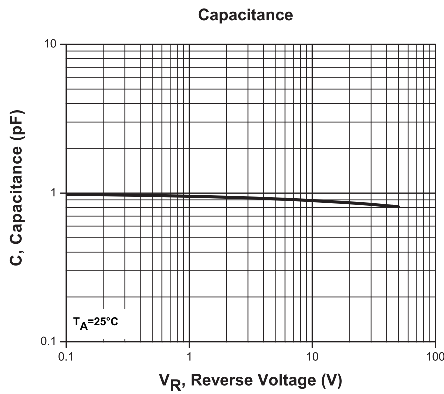
R2 (22-March 2010)

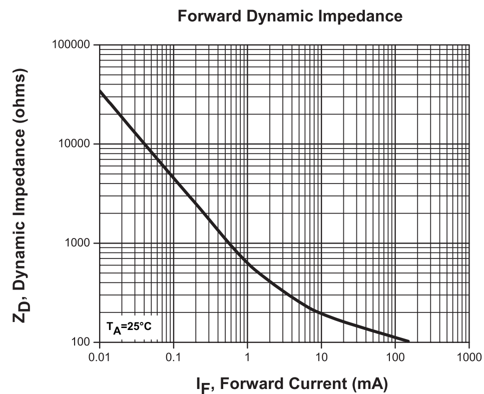
PROCESS CPD93V

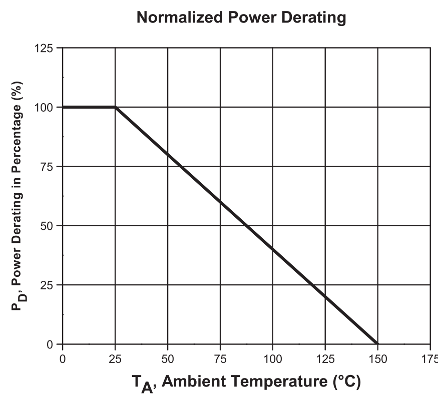
Typical Electrical Characteristics











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